

Q3 wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

IN THE ABSTRACT

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Please amend the Abstract on page 49 to read as follows:²

ABSTRACT

Q4 A hot plate for a semiconductor producing/examining device, in which hot plate, when an object to be heated such as a silicon wafer is heated in a state that the object is distanced by a certain distance from the heating face, air is less likely to stagnate between the silicon wafer and the heating face and thus the object to be heated can be evenly heated. Specifically, the hot plate for a semiconductor producing/examining device includes a resistance heating element formed on a surface of a ceramic substrate or inside the ceramic substrate, wherein the glossiness of the heating face of the ceramic substrate is 1.5% or more.

REMARKS

Favorable consideration of this application, as presently amended, is respectfully requested.

The present preliminary amendment is submitted to place the above-identified application in more proper format under United States practice.

By the present preliminary amendment the Title is amended to match that on the International publication.

²A marked-up copy of the amendment is attached hereto.